

# DATA SHEET

## **BTA204X series B and C** Three quadrant triacs high commutation

Product specification

December 1998



## Three quadrant triacs high commutation

## BTA204X series B and C

### GENERAL DESCRIPTION

Passivated high commutation triacs in a plastic full pack envelope intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. These devices will commute the full rated rms current at the maximum rated junction temperature without the aid of a snubber.

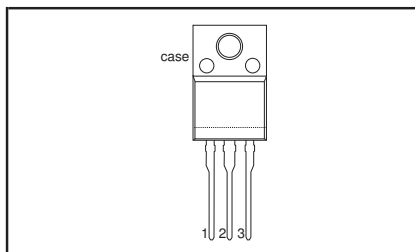
### QUICK REFERENCE DATA

| SYMBOL              | PARAMETER                                                  | MAX.                | MAX.                | MAX.                | UNIT |
|---------------------|------------------------------------------------------------|---------------------|---------------------|---------------------|------|
| $V_{\text{DRM}}$    | BTA204X-<br>BTA204X-<br>Repetitive peak off-state voltages | 500B<br>500C<br>500 | 600B<br>600C<br>600 | 800B<br>800C<br>800 | V    |
| $I_{\text{T(RMS)}}$ | RMS on-state current                                       | 4                   | 4                   | 4                   | A    |
| $I_{\text{TSM}}$    | Non-repetitive peak on-state current                       | 25                  | 25                  | 25                  | A    |

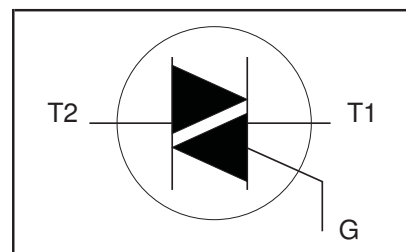
### PINNING - SOT186A

| PIN  | DESCRIPTION     |
|------|-----------------|
| 1    | main terminal 1 |
| 2    | main terminal 2 |
| 3    | gate            |
| case | isolated        |

### PIN CONFIGURATION



### SYMBOL



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL              | PARAMETER                                                    | CONDITIONS                                                                                                  | MIN. | MAX.                     |                          |             | UNIT             |
|---------------------|--------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------|------|--------------------------|--------------------------|-------------|------------------|
| $V_{\text{DRM}}$    | Repetitive peak off-state voltages                           |                                                                                                             | -    | -500<br>500 <sup>1</sup> | -600<br>600 <sup>1</sup> | -800<br>800 | V                |
| $I_{\text{T(RMS)}}$ | RMS on-state current                                         | full sine wave;<br>$T_{\text{hs}} \leq 92^\circ\text{C}$                                                    | -    | 4                        |                          |             | A                |
| $I_{\text{TSM}}$    | Non-repetitive peak on-state current                         | full sine wave;<br>$T_{\text{j}} = 25^\circ\text{C}$ prior to surge                                         | -    | 25                       |                          |             | A                |
|                     |                                                              | $t = 20\text{ ms}$                                                                                          | -    | 27                       |                          |             | A                |
|                     |                                                              | $t = 16.7\text{ ms}$                                                                                        | -    | 3.1                      |                          |             | A <sup>2</sup> s |
| $I^2t$              | $I^2t$ for fusing                                            | $t = 10\text{ ms}$                                                                                          | -    | 100                      |                          |             | A/μs             |
| $dI_{\text{T}}/dt$  | Repetitive rate of rise of on-state current after triggering | $I_{\text{TM}} = 6\text{ A}; I_{\text{G}} = 0.2\text{ A};$<br>$dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ | -    |                          |                          |             |                  |
| $I_{\text{GM}}$     | Peak gate current                                            |                                                                                                             | -    | 2                        |                          |             | A                |
| $V_{\text{GM}}$     | Peak gate voltage                                            |                                                                                                             | -    | 5                        |                          |             | V                |
| $P_{\text{GM}}$     | Peak gate power                                              |                                                                                                             | -    | 5                        |                          |             | W                |
| $P_{\text{G(AV)}}$  | Average gate power                                           | over any 20 ms period                                                                                       | -    | 0.5                      |                          |             | W                |
| $T_{\text{stg}}$    | Storage temperature                                          |                                                                                                             | -40  | 150                      |                          |             | $^\circ\text{C}$ |
| $T_{\text{j}}$      | Operating junction temperature                               |                                                                                                             | -    | 125                      |                          |             | $^\circ\text{C}$ |

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.

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### ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

| SYMBOL     | PARAMETER                                                              | CONDITIONS                                                                                    | MIN. | TYP. | MAX. | UNIT |
|------------|------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|------|------|------|------|
| $V_{isol}$ | R.M.S. isolation voltage from all three terminals to external heatsink | $f = 50\text{--}60\text{ Hz}$ ; sinusoidal waveform;<br>$R.H. \leq 65\%$ ; clean and dustfree | -    |      | 2500 | V    |
| $C_{isol}$ | Capacitance from T2 to external heatsink                               | $f = 1\text{ MHz}$                                                                            | -    | 10   | -    | pF   |

### THERMAL RESISTANCES

| SYMBOL         | PARAMETER                               | CONDITIONS                                | MIN. | TYP. | MAX. | UNIT |
|----------------|-----------------------------------------|-------------------------------------------|------|------|------|------|
| $R_{th\ j-hs}$ | Thermal resistance junction to heatsink | full or half cycle with heatsink compound | -    | -    | 5.5  | K/W  |
| $R_{th\ j-a}$  | Thermal resistance junction to ambient  | without heatsink compound in free air     | -    | 55   | 7.2  | K/W  |

### STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise stated

| SYMBOL   | PARAMETER                         | CONDITIONS                                                                           | MIN. | TYP. | MAX.        |             | UNIT |
|----------|-----------------------------------|--------------------------------------------------------------------------------------|------|------|-------------|-------------|------|
|          |                                   | <b>BTA204X-</b>                                                                      |      |      | <b>...B</b> | <b>...C</b> |      |
| $I_{GT}$ | Gate trigger current <sup>2</sup> | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$                                           | -    | -    | 50          | 35          | mA   |
|          |                                   | T2+ G+                                                                               | -    | -    | 50          | 35          | mA   |
|          |                                   | T2+ G-                                                                               | -    | -    | 50          | 35          | mA   |
| $I_L$    | Latching current                  | $V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$                                        | -    | -    | 30          | 20          | mA   |
|          |                                   | T2+ G+                                                                               | -    | -    | 45          | 30          | mA   |
|          |                                   | T2+ G-                                                                               | -    | -    | 30          | 20          | mA   |
| $I_H$    | Holding current                   | $V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$                                        | -    | -    | 30          | 20          | mA   |
| $V_T$    | On-state voltage                  | $I_T = 5\text{ A}$                                                                   | -    | 1.4  | 1.7         |             | V    |
| $V_{GT}$ | Gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$                                           | -    | 0.7  | 1.5         |             | V    |
|          |                                   | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ;<br>$T_j = 125\text{ }^{\circ}\text{C}$ | 0.25 | 0.4  | -           |             | V    |
| $I_D$    | Off-state leakage current         | $V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$                           | -    | 0.1  | 0.5         |             | mA   |

### DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise stated

| SYMBOL        | PARAMETER                                      | CONDITIONS                                                                                                                                                 | MIN.        |             | TYP. | UNIT             |
|---------------|------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|-------------|------|------------------|
|               |                                                | <b>BTA204X-</b>                                                                                                                                            | <b>...B</b> | <b>...C</b> |      |                  |
| $dV_D/dt$     | Critical rate of rise of off-state voltage     | $V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ;<br>exponential waveform; gate open circuit                                            | 1000        | 1000        | -    | V/ $\mu\text{s}$ |
| $dI_{com}/dt$ | Critical rate of change of commutating current | $V_{DM} = 400\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 4\text{ A}$ ;<br>$dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit | 6           | 3           | -    | A/ms             |
| $t_{gt}$      | Gate controlled turn-on time                   | $I_{TM} = 12\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1\text{ A}$ ;<br>$dI_G/dt = 5\text{ A}/\mu\text{s}$                                               | -           | -           | 2    | $\mu\text{s}$    |

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

# Three quadrant triacs high commutation

## BTA204X series B and C

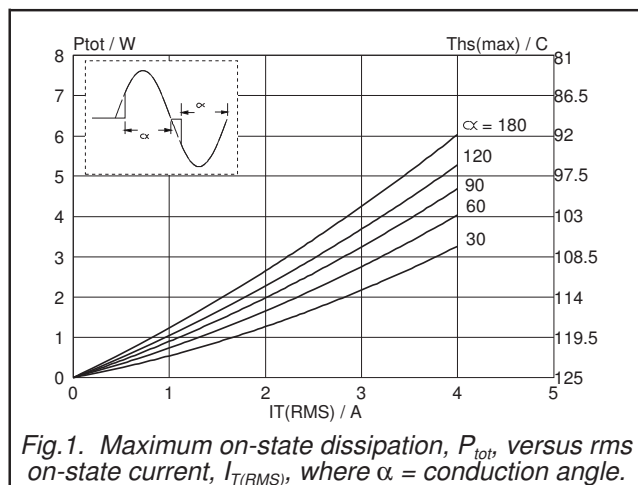


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

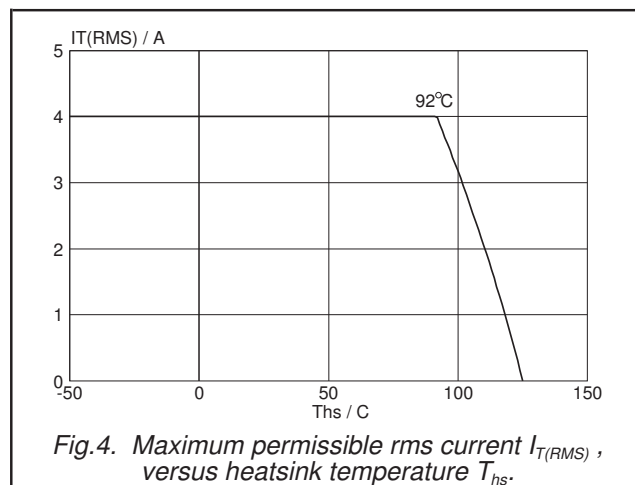


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus heatsink temperature  $T_{hs}$ .

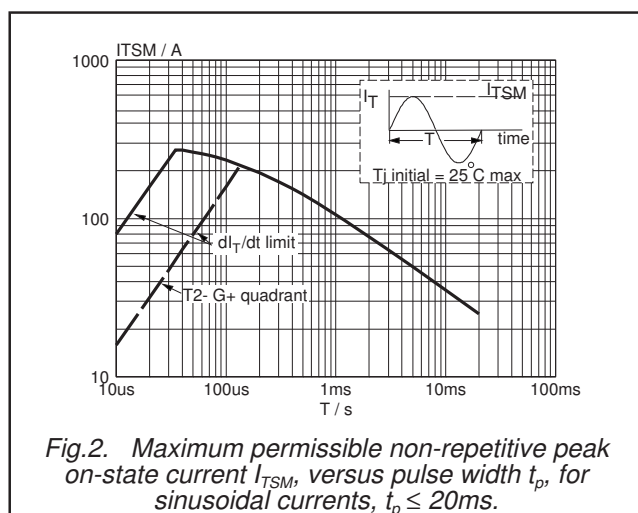


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20\text{ms}$ .

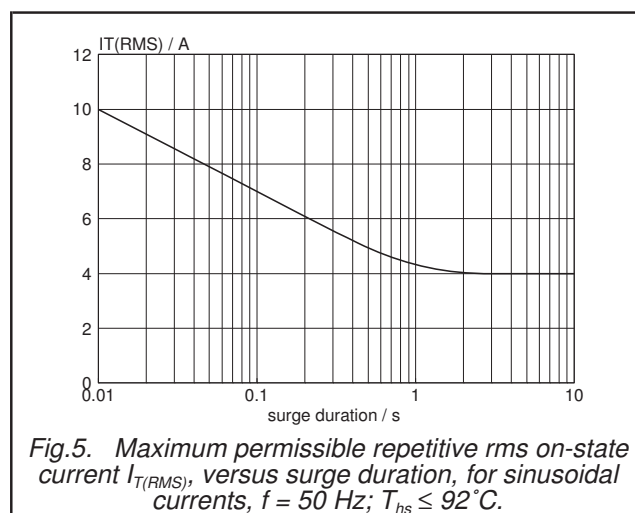


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50\text{ Hz}$ ;  $T_{hs} \leq 92^\circ\text{C}$ .

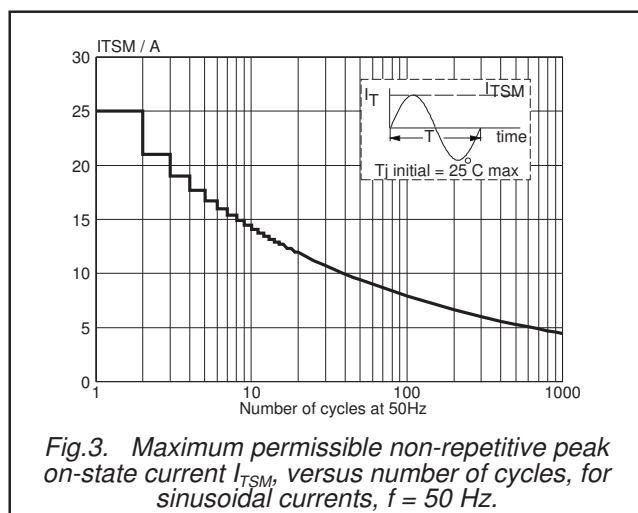


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50\text{ Hz}$ .

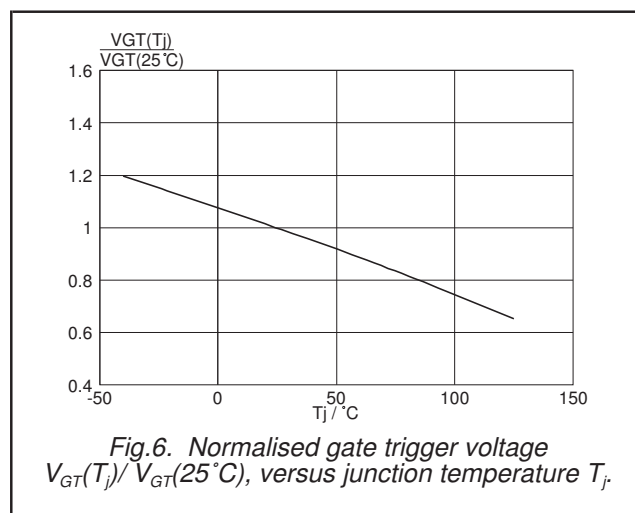
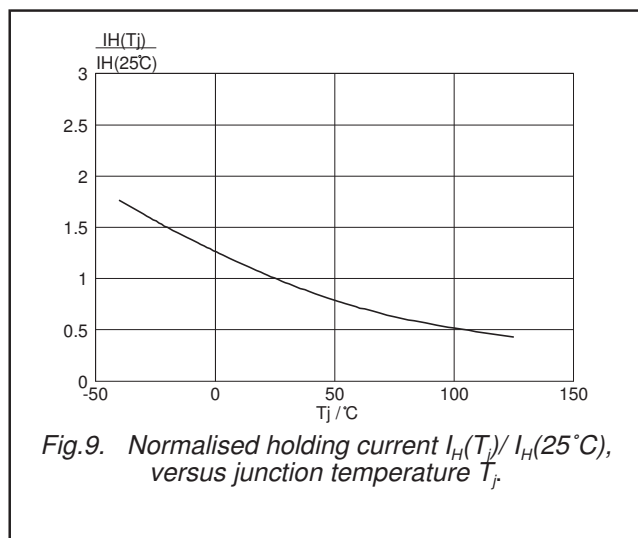
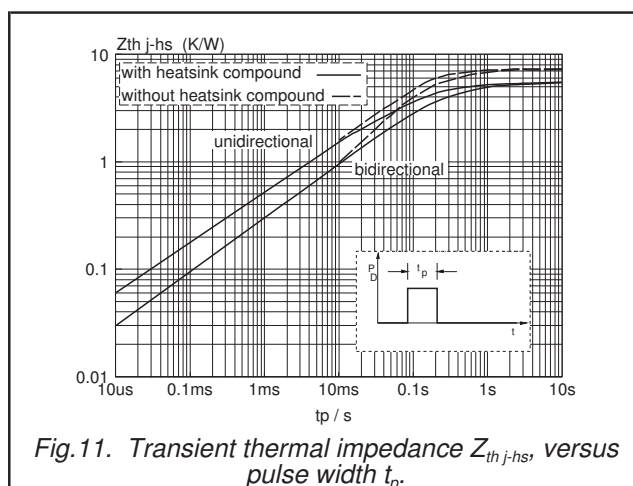
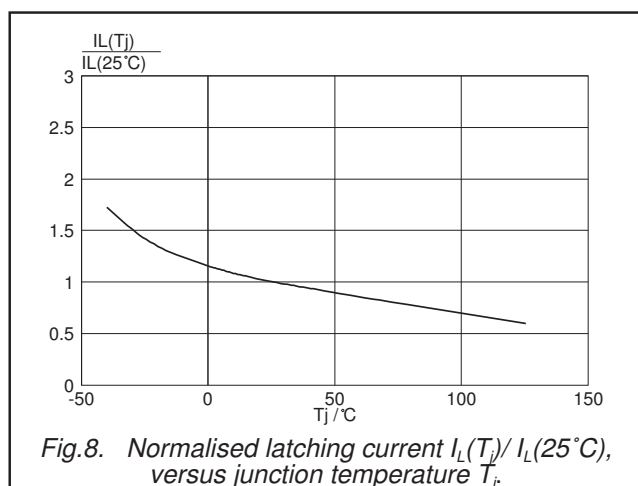
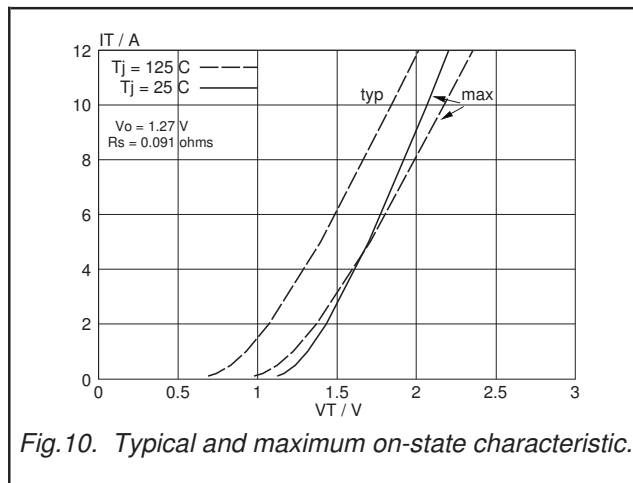
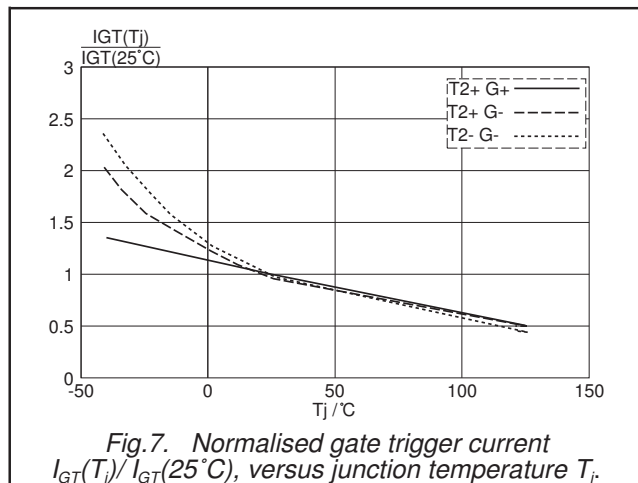


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

# Three quadrant triacs high commutation

## BTA204X series B and C



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### MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

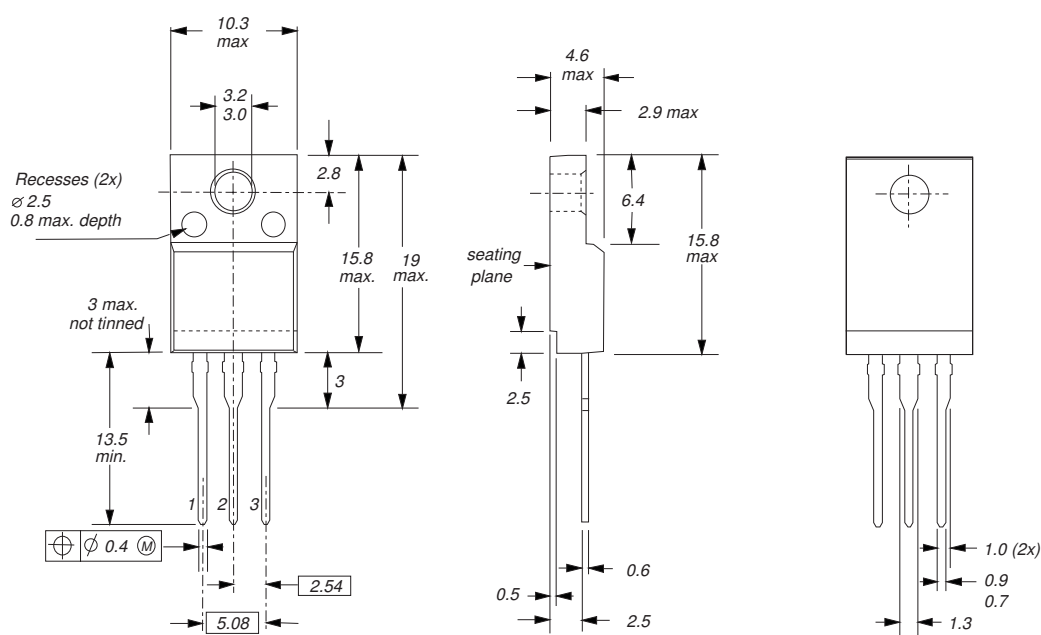


Fig.12. SOT186A; The seating plane is electrically isolated from all terminals.

### Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

## Legal information

### DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
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| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
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